IXYS

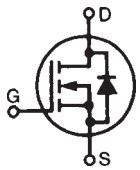
Advanced Technical Information

PolarHT™ Power MOSFET

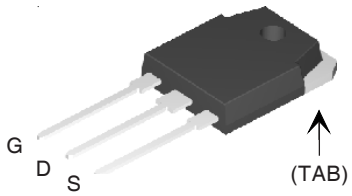
IXTQ 75N10P
IXTA 75N10P
IXTP 75N10P

V_{DSS} = 100 V
I_{D25} = 75 A
$R_{DS(on)}$ = 25 mΩ

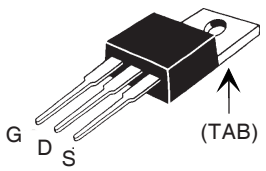
N-Channel Enhancement Mode



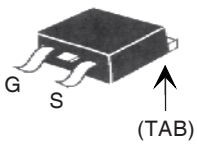
TO-3P (IXTQ)



TO-220 (IXTP)



TO-263 (IXTA)



G = Gate D = Drain
S = Source TAB = Drain

Symbol	Test Conditions	Maximum Ratings	
V_{DSS}	T_J = 25°C to 175°C	100	V
V_{DGR}	T_J = 25°C to 175°C; R_{GS} = 1 MΩ	100	V
V_{GSM}		±20	V
I_{D25}	T_C = 25°C	75	A
I_{DM}	T_C = 25°C, pulse width limited by T_{JM}	200	A
I_{AR}	T_C = 25°C	50	A
E_{AR}	T_C = 25°C	30	mJ
E_{AS}	T_C = 25°C	1.0	J
dv/dt	$I_S \le I_{DM}$, di/dt ≤ 100 A/μs, $V_{DD} \le V_{DSS}$, $T_J \le 150°C$, R_G = 10 Ω	10	V/ns
P_D	T_C = 25°C	300	W
T_J		-55 ... +150	°C
T_{JM}		150	°C
T_{stg}		-55 ... +150	°C
T_L	1.6 mm (0.062 in.) from case for 10 s	300	°C
	Maximum tab temperature for soldering TO-263 package for 10s	260	°C
M_d	Mounting torque (TO-3P / TO-220)	1.13/10	Nm/lb.in.
Weight	TO-3P	5.5	g
	TO-220	4	g
	TO-263	3	g

Symbol	Test Conditions (T_J = 25°C, unless otherwise specified)	Characteristic Values Min.	Typ.	Max.	
V_{DSS}	V_{GS} = 0 V, I_D = 250 μA	100			V
$V_{GS(th)}$	$V_{DS} = V_{GS}$, I_D = 250μA	2.5		5.0	V
I_{GSS}	V_{GS} = ±20 V_{DC}, V_{DS} = 0			±100	nA
I_{DSS}	$V_{DS} = V_{DSS}$, V_{GS} = 0 V			25	μA
	T_J = 125°C			250	μA
$R_{DS(on)}$	V_{GS} = 10 V, $I_D = 0.5\ I_{D25}$, Pulse test, t ≤ 300 μs, duty cycle d ≤ 2 %		21	25	mΩ

Features

- International standard packages
- Unclamped Inductive Switching (UIS) rated
- Low package inductance
  - easy to drive and to protect

Advantages

- Easy to mount
- Space savings
- High power density

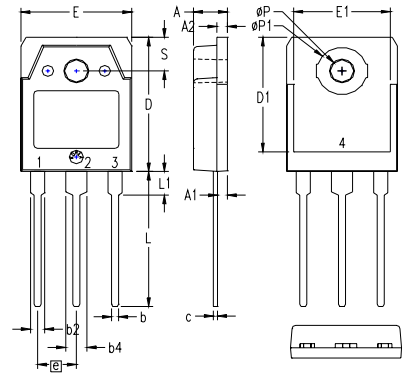
PolarHT™ DMOS transistors utilize proprietary designs and process. US patent is pending.

Symbol	Test Conditions	Characteristic Values (T_J = 25°C, unless otherwise specified) Min.	Typ.	Max.
g_{fs}	V_{DS}= 10 V; I_D = 0.5 I_{D25}, pulse test	20	28	S
C_{iss}	V_{GS} = 0 V, V_{DS} = 25 V, f = 1 MHz		2250	pF
C_{oss}			890	pF
C_{rss}			275	pF
$t_{d(on)}$	V_{GS} = 10 V, V_{DS} = 0.5 V_{DSS}, I_D = I_{D25} R_G = 10 Ω (External)		27	ns
t_r			53	ns
$t_{d(off)}$			66	ns
t_f			45	ns
$Q_{g(on)}$	V_{GS}= 10 V, V_{DS} = 0.5 V_{DSS}, I_D = 0.5 I_{D25}		74	nC
Q_{gs}			18	nC
Q_{gd}			40	nC
R_{thJC}				0.42 K/W
R_{thCK}	(TO-3P)		0.21	K/W
	(TO-220)		0.25	K/W

Source-Drain Diode

Symbol	Test Conditions (T_J = 25°C, unless otherwise specified)	Characteristic Values Min.	typ.	Max.
I_S	V_{GS} = 0 V			75 A
I_{SM}	Repetitive			200 A
V_{SD}	I_F = I_S, V_{GS} = 0 V, Pulse test, t ≤ 300 µs, duty cycle d ≤ 2 %			1.5 V
t_{rr}	I_F = 25 A -di/dt = 100 A/µs		120	ns
Q_{RM}	V_R = 75 V		1.4	µC

TO-3P (IXTQ) Outline

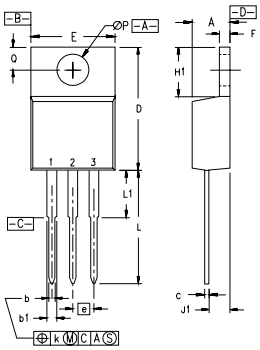


1 – GATE
2 – DRAIN (COLLECTOR)
3 – SOURCE (EMITTER)
4 – DRAIN (COLLECTOR)

SYM	INCHES MIN	INCHES MAX	MILLIMETERS MIN	MILLIMETERS MAX
A	.185	.193	4.70	4.90
A1	.051	.059	1.30	1.50
A2	.057	.065	1.45	1.65
b	.035	.045	0.90	1.15
b2	.075	.087	1.90	2.20
b4	.114	.126	2.90	3.20
c	.022	.031	0.55	0.80
D	.780	.791	19.80	20.10
D1	.665	.677	16.90	17.20
E	.610	.622	15.50	15.80
E1	.531	.539	13.50	13.70
e	.215 BSC		5.45 BSC	
L	.779	.795	19.80	20.20
L1	.134	.142	3.40	3.60
øP	.126	.134	3.20	3.40
øP1	.272	.280	6.90	7.10
S	.193	.201	4.90	5.10

All metal area are tin plated.

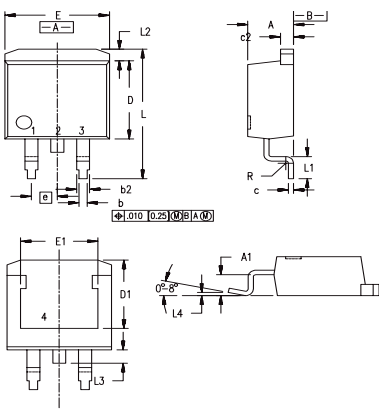
TO-220 (IXTA) Outline



Pins: 1 - Gate 2 - Drain

SYM	INCHES MIN	INCHES MAX	MILLIMETERS MIN	MILLIMETERS MAX
A	.170	.190	4.32	4.83
b	.025	.040	0.64	1.02
b1	.045	.065	1.15	1.65
c	.014	.022	0.35	0.56
D	.580	.630	14.73	16.00
E	.390	.420	9.91	10.66
e	.100 BSC		2.54 BSC	
F	.045	.055	1.14	1.40
H1	.230	.270	5.85	6.85
J1	.090	.110	2.29	2.79
k	0	.015	0	0.38
L	.500	.550	12.70	13.97
L1	.110	.230	2.79	5.84
ØP	.139	.161	3.53	4.08
Q	.100	.125	2.54	3.18

TO-263 (IXTP) Outline



Dim.	Millimeter Min.	Millimeter Max.	Inches Min.	Inches Max.
A	4.06	4.83	.160	.190
A1	2.03	2.79	.080	.110
b	0.51	0.99	.020	.039
b2	1.14	1.40	.045	.055
c	0.46	0.74	.018	.029
c2	1.14	1.40	.045	.055
D	8.64	9.65	.340	.380
D1	7.11	8.13	.280	.320
E	9.65	10.29	.380	.405
E1	6.86	8.13	.270	.320
e	2.54	BSC	.100	BSC
L	14.61	15.88	.575	.625
L1	2.29	2.79	.090	.110
L2	1.02	1.40	.040	.055
L3	1.27	1.78	.050	.070
L4	0	0.38	0	.015
R	0.46	0.74	.018	.029

Fig. 1. Output Characteristics @ 25°C

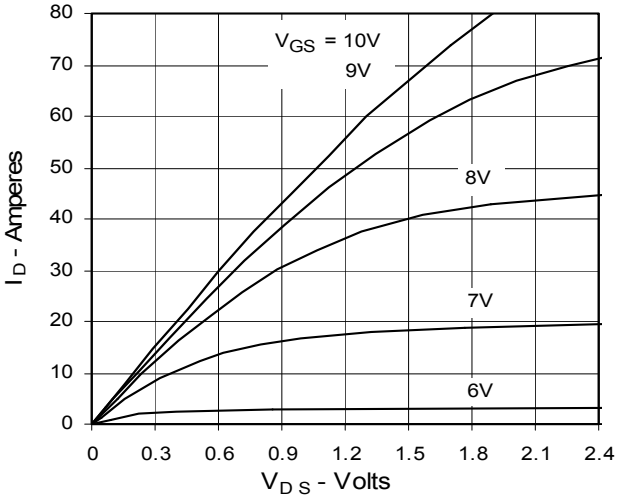


Fig. 2. Extended Output Characteristics @ 25°C

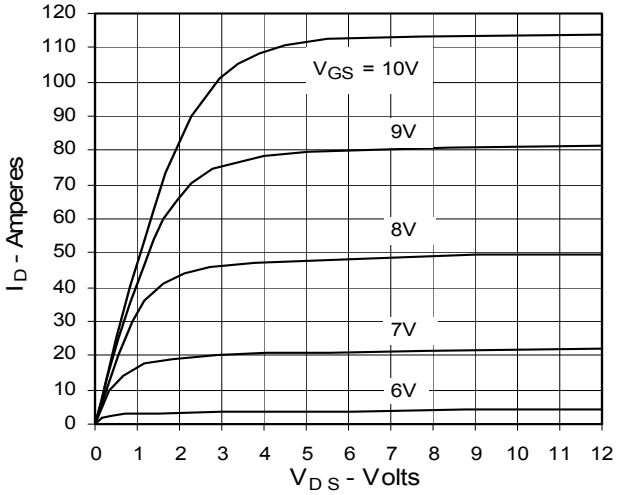


Fig. 3. Output Characteristics @ 125°C

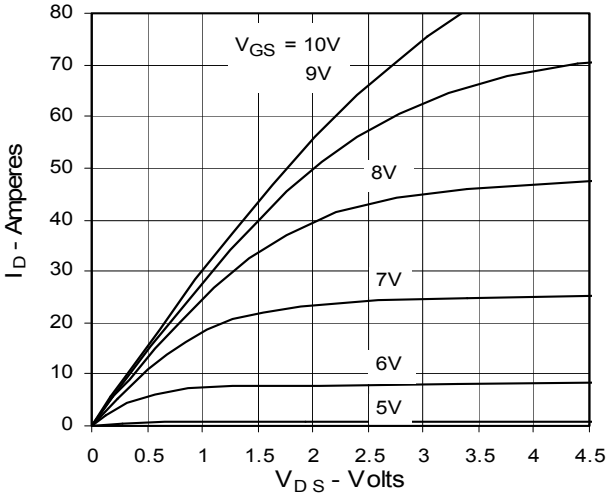


Fig. 4. $R_{DS(on)}$ Normalized to 0.5 I_{D25} Value vs. Junction Temperature

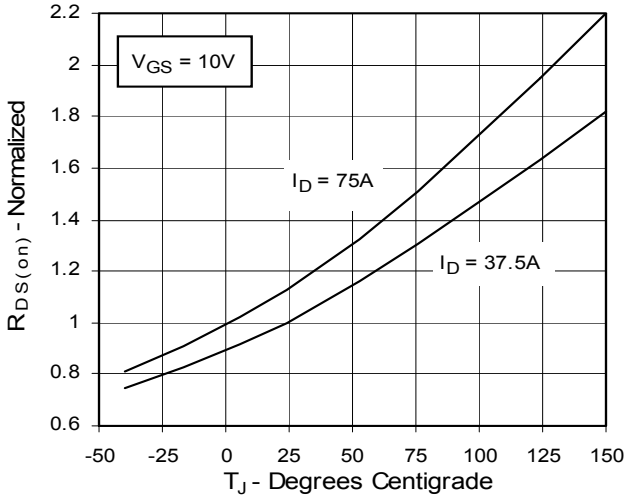


Fig. 5. $R_{DS(on)}$ Normalized to 0.5 I_{D25} Value vs. I_D

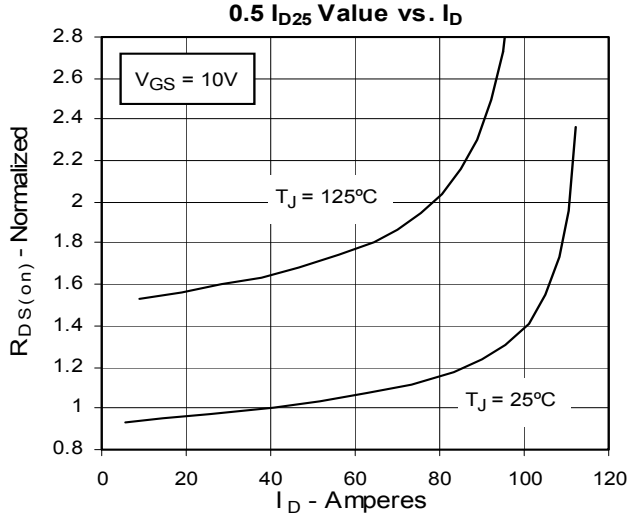


Fig. 6. Drain Current vs. Case Temperature

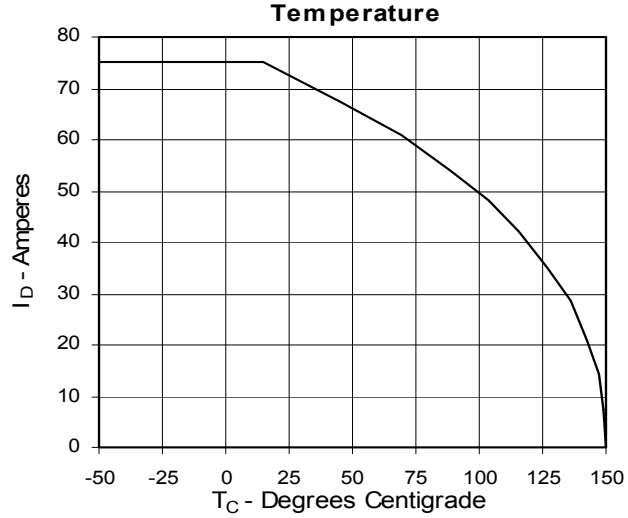


Fig. 7. Input Admittance

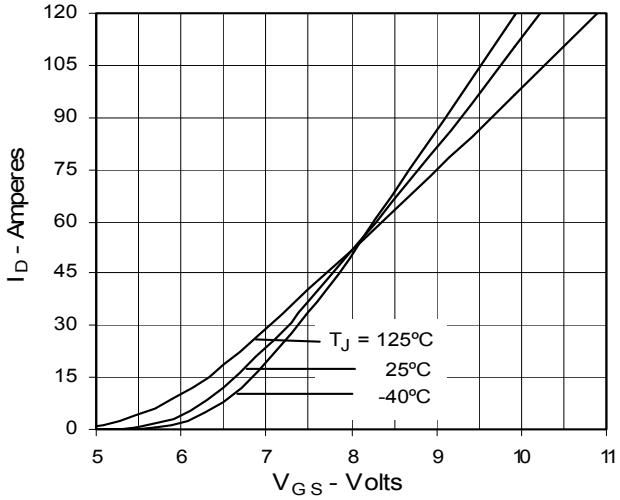


Fig. 8. Transconductance

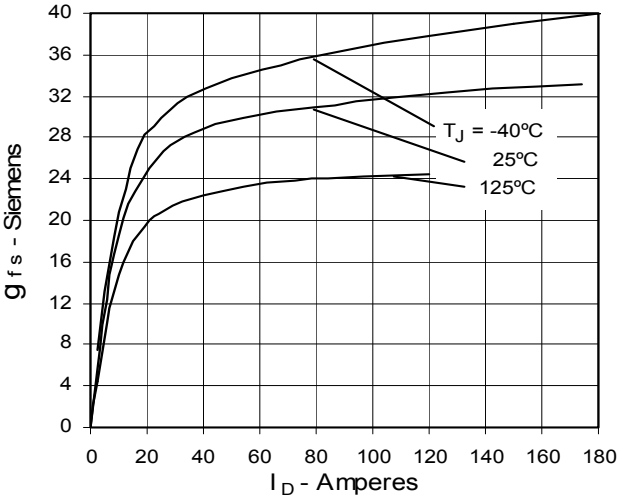


Fig. 9. Source Current vs. Source-To-Drain Voltage

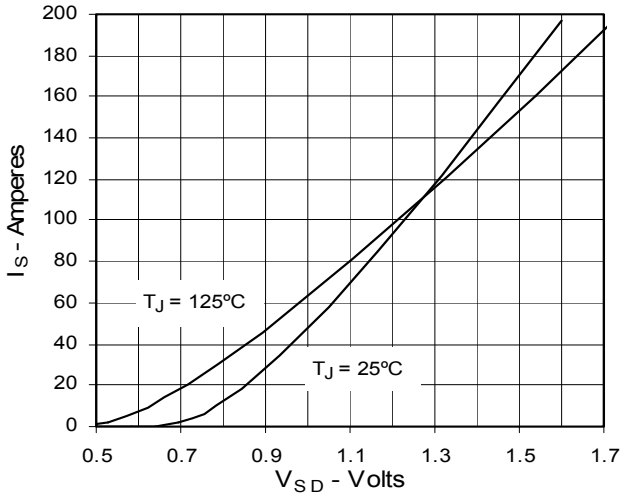


Fig. 10. Gate Charge

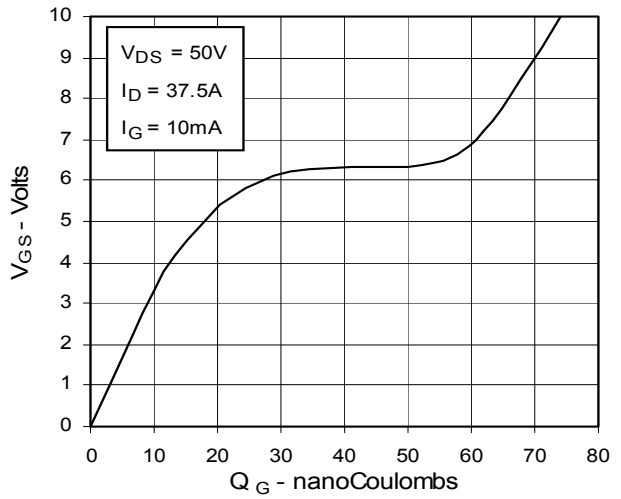


Fig. 11. Capacitance

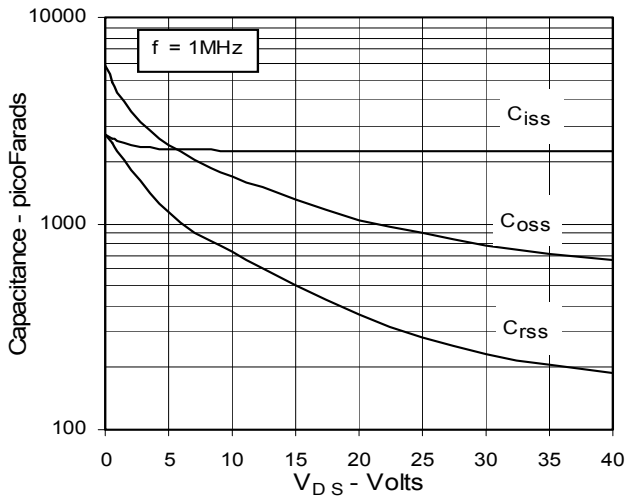


Fig. 12. Forward-Bias Safe Operating Area

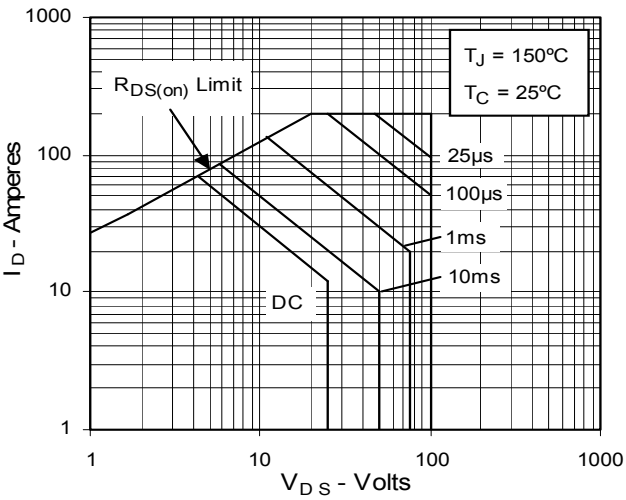


Fig. 13. Maximum Transient Thermal Resistance